

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
6 April 2006 (06.04.2006)

PCT

(10) International Publication Number
WO 2006/035952 A1

(51) International Patent Classification:
H01L 51/50 (2006.01)

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(21) International Application Number:
PCT/JP2005/018215

(22) International Filing Date:
26 September 2005 (26.09.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2004-288408 30 September 2004 (30.09.2004) JP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KM, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, LY,
MA, MD, MG, MK, MN, MW, MX, MZ, NA, NG, NI, NO,
NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK,
SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ,
VC, VN, YU, ZA, ZM, ZW.

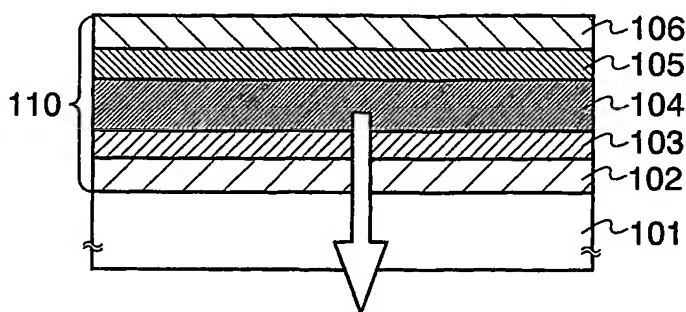
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT,
RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA,
GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: LIGHT EMITTING ELEMENT AND DISPLAY DEVICE USING THE SAME



(57) Abstract: An object of the
invention is to provide a highly
reliable light emitting element with
low drive voltage and longer life than
a conventional light emitting element,
and a display device using the light
emitting element. A light emitting
element according to the invention
comprises a plurality of layers which is
interposed between a pair of electrodes,
in which at least one of the plurality of
layers is formed of a layer containing
a light emitting material, and the layer
containing a light emitting material is

interposed between a layer containing an oxide semiconductor and/or metal oxide and a material having a higher hole transporting property than an electron transporting property, and a layer containing an oxide semiconductor and/or metal oxide, a material having a higher electron transporting property than a hole transporting property and a material which can donate electrons to the material having a higher electron transporting property than a hole transporting property.